SAMYANG ELECTRONICS

LS22 --- LS220

SCHOTTKY BARRIER RECTIFIER

VOLTAGE RANGE: 20 --- 200 V
CURRENT: 2.0 A

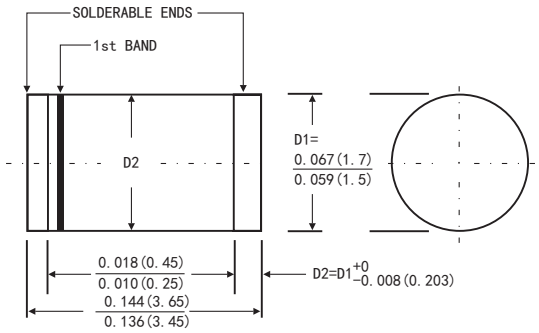
FEATURES

- Plastic package has Underwriters Laboratory Flammability Classification 94V-0
- Metal silicon junction ,majority carrier conduction
- Guard ring for overvoltage protection
- Built-in strain relief
- For surface mounted applications
- Low profile package
- Low power loss ,high efficiency
- High current capability ,Low forward voltage drop
- High surge capability
- For use in low voltage ,high frequency inverters, free wheeling , and polarity protection applications
- High temperature soldering guaranteed:260 C/10 seconds at terminals
- Component in accordance to RoHS 2002/95/EC and WEEE 2002/96/EC

MECHANICAL DATA

- Case : JEDEC Mini MELF(DO-213AA) molded plastic body
- Terminals: Solder Plated, solderable per MIL-STD-750,method 2026
- Polarity : Color band denotes cathode end
- Mounting Position : Any
- Weight : 0.0005ounce, 0.015 gram

MiniMELF(DO-213AA)



Dimensions in inches and (millimeters)

MAXIMUM RATINGS AND ELECTRICAL CHARACTERISTICS

Ratings at 25 C ambient temperature unless otherwise specified.

Single phase,half wave,60 Hz,resistive or inductive load. For capacitive load,derate by 20%.

	Symbols	LS 22	LS 23	LS 24	LS 25	LS 26	LS 28	LS 210	LS 215	LS 220	Volts
Maximum repetitive peak reverse voltage	V_{RRM}	20	30	40	50	60	80	100	150	200	Volts
Maximum RMS voltage	V_{RMS}	14	21	28	35	42	57	71	105	140	Volts
Maximum DC blocking voltage	V_{DC}	20	30	40	50	60	80	100	150	200	Volts
Maximum average forward rectified current (See Fig. 1)	$I_{(AV)}$	2.0									Amps
Peak forward surge current 8.3ms single half sine-wave superimposed on rated load (JEDEC method)	I_{FSM}	50.0									Amps
Maximum instantaneous forward voltage at 2.0 A(note 1)	V_F	0.55			0.75		0.85		0.90	0.95	Volts
Maximum instantaneous reverse current at rated DC blocking voltage(Note 1) T_A=25℃	I_R	0. 2									mA
T_A=100℃		10.0									
Typical thermal resistance (Note 2)	R_{JA} R_{JL}	75.0 30.0									℃/W
Operating junction temperature range	T_J	-65 to+150									℃
Storage temperature range	T_{STG}	-65 to+150									℃

NOTE: 1. Measured at 1.0MHz and applied reverse voltage of 4.0V DC.

2. Thermal resistance from junction to ambient.

FIG.1-FORWARD CURRENT DERATING CURVE

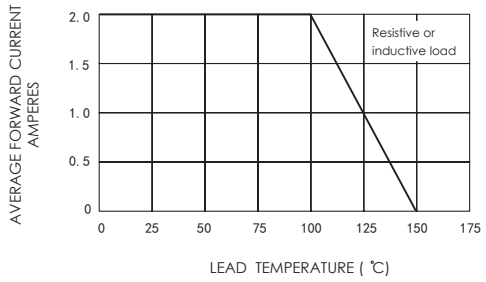


FIG.2-MAXIMUM NON-REPETITIVE PEAK FORWARD SURGE CURRENT

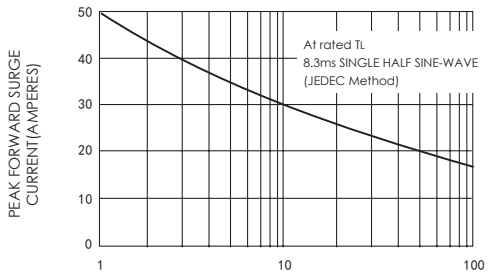


FIG.3-TYPICAL INSTANTANEOUS FORWARD CHARACTERISTICS

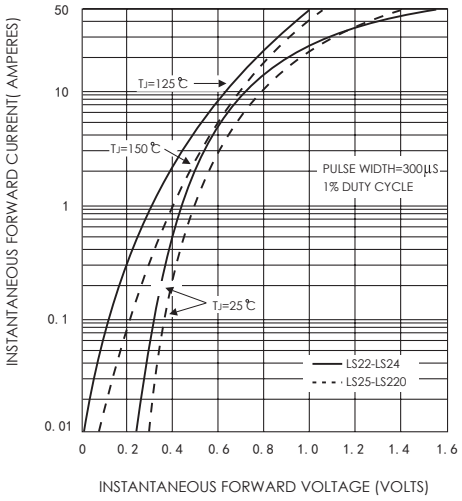


FIG.4-TYPICAL REVERSE CHARACTERISTICS

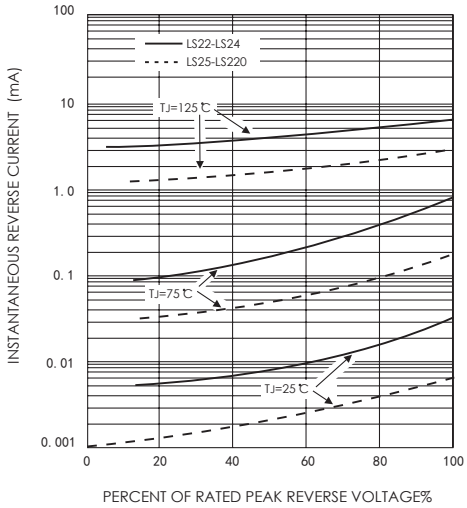


FIG.5-TYPICAL JUNCTION CAPACITANCE

